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Customer Number

Patent
Case No.: 58434US002

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

First Named Inventor: MUYRES, DAWN V.

Application No.: 10/642919

Confirmation No.: 3648

Filed: August 18, 2003

Title: METHOD FOR SEALING THIN FILM TRANSISTORS

RESPONSE TO RESTRICTION REQUIREMENTMail Stop Amendment
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

CERTIFICATE OF MAILING OR TRANSMISSION [37 CFR § 1.8(a)]

I hereby certify that this correspondence is being:

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JAN 23 2008

Date

Signed by: Hylis H. Froelke

Dear Sir:

This is in response to the Office Action dated December 31, 2007. Claims 1 - 30 are pending.

Restriction Requirement

Claims 1 - 30 were restricted under 35 U.S.C. § 121 as follows:

- I. Claims 1 - 11 and 13 - 28, said to be drawn to a method of producing a thin film transistor, classified in Class 438, subclass 99;
- II. Claims 12 and 29, said to be drawn to the method of Invention I in combination with a surface treatment layer, classified in Class 438, subclass 99; and
- II. Claim 30, said to be drawn to a thin film transistor, classified in class 257, subclass 40.

In response, Applicants hereby elect Invention I, claims 1 - 11 and 13 - 28, without traverse.

Species Election

The Examiner has also required under 35 U.S.C. § 121 that if Applicants elect Invention I, they must also elect one of the following species:

IA. The species of Invention I with a single aperture mask used to form the gate electrode, dielectric, semiconductor, source/drain, and sealing material; or

IB. The species of Invention II with different aperture masks used to form the gate electrode, dielectric, semiconductor, source/drain, and sealing material.

In response, Applicants hereby elect species IB, which is described by claim 28. Applicants assume that this requirement to elect a species applies only to claims 18 – 29. Accordingly, claims 18 – 26, 28 and 29 read on the elected species.

Concluding Remarks

Applicants have elected Invention I, species IB. Continued prosecution of this application is respectfully requested.

Respectfully submitted,

Jan. 23, 2008
Date

By: Lisa P. Fulton
Lisa P. Fulton, Reg. No.: 55,195
Telephone No.: 651-733-1260

Office of Intellectual Property Counsel
3M Innovative Properties Company
Facsimile No.: 651-736-3833